

Title (en)

WAFER STRUCTURE FOR ELECTRONIC INTEGRATED CIRCUIT MANUFACTURING

Title (de)

WAFERSTRUKTUR ZUR HERSTELLUNG EINER ELEKTRONISCHEN INTEGRIERTEN SCHALTUNG

Title (fr)

STRUCTURE DE TRANCHE POUR LA FABRICATION DE CIRCUITS INTÉGRÉS ÉLECTRONIQUES

Publication

**EP 2748847 A4 20160601 (EN)**

Application

**EP 12826159 A 20120824**

Priority

- US 201113218308 A 20110825
- US 201113218273 A 20110825
- US 201113218335 A 20110825
- US 201113218345 A 20110825
- US 201113218352 A 20110825
- US 201113218292 A 20110825
- US 2012052293 W 20120824

Abstract (en)

[origin: WO2013028973A1] A bonded wafer structure having a handle wafer, a device wafer, and an interface region with an abrupt transition between the conductivity profile of the device wafer and the handle wafer is used for making semiconductor devices. The improved doping profile of the bonded wafer structure is well suited for use in the manufacture of integrated circuits. The bonded wafer structure is especially suited for making radiation-hardened integrated circuits.

IPC 8 full level

**H01L 21/18** (2006.01); **H01L 21/329** (2006.01); **H01L 21/8238** (2006.01); **H01L 29/32** (2006.01); **H01L 29/36** (2006.01); **H01L 29/868** (2006.01); **H01L 27/088** (2006.01); **H01L 27/092** (2006.01)

CPC (source: EP)

**H01L 21/187** (2013.01); **H01L 21/263** (2013.01); **H01L 27/088** (2013.01); **H01L 27/092** (2013.01); **H01L 29/32** (2013.01); **H01L 29/36** (2013.01); **H01L 29/66136** (2013.01); **H01L 29/868** (2013.01)

Citation (search report)

- [X] EP 0327316 A2 19890809 - TOSHIBA KK [JP]
- [X] US 4935386 A 19900619 - NAKAGAWA AKIO [JP], et al
- [X] EP 0889509 A2 19990107 - HARRIS CORP [US]
- [X] CHING-FA YEH ET AL: "THE NOVEL PREPARATION OF P-N JUNCTION MESA DIODES BY SILICON-WAFER DIRECT BONDING (SDB)", JAPANESE JOURNAL OF APPLIED PHYSICS, JAPAN SOCIETY OF APPLIED PHYSICS, JP, vol. 31, no. 5A, 1 May 1992 (1992-05-01), pages 1535 - 1540, XP000355403, ISSN: 0021-4922, DOI: 10.1143/JJAP.31.1535
- See references of WO 2013028983A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

**WO 2013028973 A1 20130228**; EP 2748844 A1 20140702; EP 2748844 A4 20151104; EP 2748845 A1 20140702; EP 2748845 A4 20150708; EP 2748846 A1 20140702; EP 2748846 A4 20151111; EP 2748847 A1 20140702; EP 2748847 A4 20160601; EP 2748848 A1 20140702; EP 2748848 A4 20150610; EP 2748849 A2 20140702; EP 2748849 A4 20151216; WO 2013028976 A1 20130228; WO 2013028983 A1 20130228; WO 2013028986 A1 20130228; WO 2013028988 A1 20130228; WO 2013081694 A2 20130606; WO 2013081694 A3 20131024

DOCDB simple family (application)

**US 2012052269 W 20120824**; EP 12825109 A 20120824; EP 12825755 A 20120824; EP 12825811 A 20120824; EP 12826159 A 20120824; EP 12826508 A 20120824; EP 12854047 A 20120824; US 2012052264 W 20120824; US 2012052280 W 20120824; US 2012052293 W 20120824; US 2012052299 W 20120824; US 2012052302 W 20120824